



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

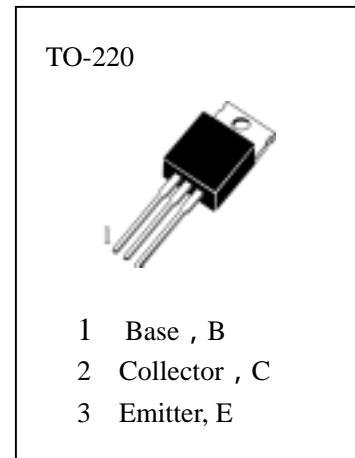
HE3055

GENERAL PURPOSE AND SWITCHING APPLICATIONS

DCCURRENT GAIN SPECIFIED TO 10 AMPERES

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg} —Storage Temperature.....	-55~150
T_j —Junction Temperature.....	150
P_C —Collector Dissipation ($T_c=25^\circ C$)	75W
P_C —Collector Dissipation ($T_A=25^\circ C$)	0.6W
V_{CBO} —Collector-Base Voltage.....	70V
V_{CEO} —Collector-Emitter Voltage.....	60V
V_{EBO} —Emitter-Base Voltage.....	5V
I_C —Collector Current (DC)	10A
I_B —Base Current.....	6A



电参数 ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CEO}	Collector-Emitter Sustaining Voltage	60			V	$I_C=10mA, I_B=0$
I_{CEO}	Collector Cutoff Current			0.7	mA	$V_{CE}=30V, I_B=0$
I_{EBO}	Emitter-Base Cutoff Current			5	mA	$V_{EB}=5V, I_C=0$
$HFE(1)$	DC Current Gain	20		100		$V_{CE}=4V, I_C=4A$
$HFE(2)$		5				$V_{CE}=4V, I_C=10A$
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage			1.1	V	$I_C=4A, I_B=400mA$
$V_{CE(sat2)}$				8	V	$I_C=10A, I_B=3.3mA$
$V_{BE(on)}$	Base- Emitter Saturation Voltage			1.8	V	$V_{CE}=4V, I_C=4A$
f_T	Current Gain-Bandwidth Product	2.0				$V_{CE}=10V, I_C=500mA$ $f=500KHz$